Technische Information / Technical Information

Type: IGBT-Module
Manufacturer: Fuji Electric Fuji_2MBI200XAA065-50

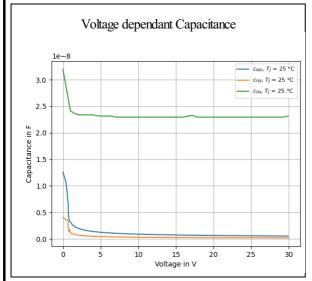


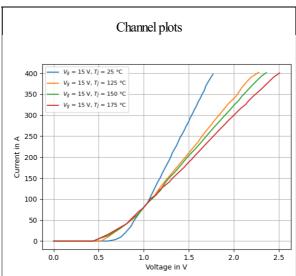
Transistor Specifications	Value	Units
Author	Nikolas Förster	-
C_iss_fix	2.3e-08	F
C_oss_fix	9e-10	F
C_rss_fix	3.1e-10	F
Cooling_area	0.003196	sq.m
Datasheet_date	2019-05	-
Datasheet_hyperlink	Fuji Electric	-
Housing_area	0.003196	sq.m
Housing_type	M263	-
I_abs_max	400	A
I_cont	200	A
Manufacturer	Fuji Electric	-
Name	Fuji_2MBI200XAA065-50	-
R_g_int	3	Ohms
R_th_cs	0.05	Ohms
T_c_max	125	°C
Туре	IGBT	-
V_abs_max	650	V

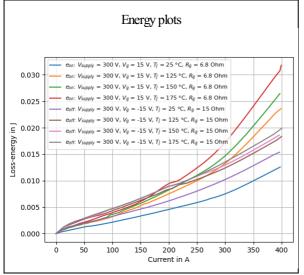
IGBT Specifications			
T_j_max	175	°C	
R_th_total	0.238	Ohms	

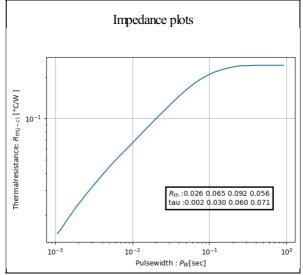
Diode Specifications			
T_j_max	175	°C	
R_th_total	0.457	Ohms	

IGBT Characteristic Plots









Diode Characteristic Plots

